

isc N-Channel MOSFET Transistor

2SK1350

DESCRIPTION

- Drain Current $-I_D=15A@ T_C=25^{\circ}C$
- Drain Source Voltage-
: $V_{DSS}=200V(\text{Min})$
- Fast Switching Speed
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

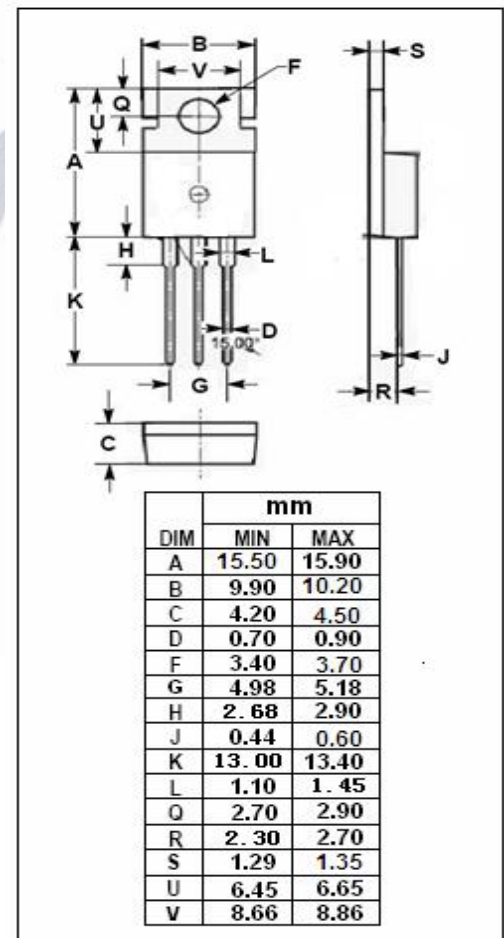
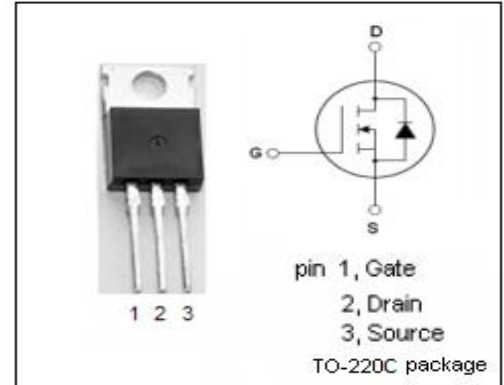
- high speed power switching

ABSOLUTE MAXIMUM RATINGS($T_a=25^{\circ}C$)

SYMBOL	ARAMETER	VALUE	UNIT
V_{DSS}	Drain-Source Voltage ($V_{GS}=0$)	200	V
V_{GS}	Gate-Source Voltage	± 20	V
I_D	Drain Current-continuous@ $TC=25^{\circ}C$	15	A
P_{tot}	Total Dissipation@ $TC=25^{\circ}C$	125	W
T_j	Max. Operating Junction Temperature	150	$^{\circ}C$
T_{stg}	Storage Temperature Range	-55~150	$^{\circ}C$

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th j-c}$	Thermal Resistance,Junction to Case	1.0	$^{\circ}C/W$
$R_{th j-a}$	Thermal Resistance,Junction to Ambient	62	$^{\circ}C/W$



isc N-Channel Mosfet Transistor**2SK1350****• ELECTRICAL CHARACTERISTICS (T_c=25°C)**

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP	MAX	UNIT
V _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} =0; I _D = 10mA	200			V
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =10 V _{GS} ; I _D =1mA	1.5		3.5	V
R _{DS(on)}	Drain-Source On-stage Resistance	V _{GS} =10V; I _D =10A		0.14	0.18	Ω
I _{GSS}	Gate Source Leakage Current	V _{GS} = ±20V; V _{DS} = 0			±100	nA
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =200V; V _{GS} = 0			300	uA
V _{SD}	Diode Forward Voltage	I _F =15A; V _{GS} =0			2.0	V
t _r	Rise time	V _{GS} =10V; I _D =10A; R _L =10 Ω		30	60	ns
t _{on}	Turn-on time			45	90	ns
t _f	Fall time			30	60	ns
t _{off}	Turn-off time			70	140	ns